Product data sheet

1. General description

Dual ultrafast power diode in a SOT78 (TO-220AB) plastic package.

2. Features and benefits

- Ultra low leakage current
- High junction temperature up to 175 °C
- Low on-state loss
- Fast switching
- Soft recovery characteristic minimizes power consuming oscillations
- High reverse surge capability
- High thermal cycling performance
- Low thermal resistance

3. Applications

Home appliance power supply

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Values				Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			2	200		V
I _{O(AV)}	average output current	δ = 0.5; T _{mb} ≤ 149 °C; Square-wave pulse		:	20		Α
I _{RRM}	repetitive peak reverse current	δ = 0.001; t_p = 2 μ s; per diode	0.2			А	
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k Ω ; all pins	8				kV
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode; Fig. 4	125			А	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage $I_F = 8 \text{ A}; T_j = 150 \text{ °C}; Fig. 6$			-	0.76	0.85	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/µs};$ $T_j = 25 \text{ °C}; Fig. 7$		-	18	25	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode		A1
3	A2	anode 2		A1 A2 K Sym125

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BYV32E-200P	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

7. Marking

Table 4. Marking codes

3	
Type number	Marking codes
BYV32E-200P	BYV32E-200P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		200	V
V_{RWM}	crest working reverse voltage		200	V
V_R	reverse voltage	DC	200	V
I _{F(AV)}	average forward current	$δ = 0.5$; $T_{mb} \le 149$ °C; Square-ware pulse; Fig. 1; Fig. 2; Fig. 3	10	А
I _{O(AV)}	average output current	δ = 0.5; T _{mb} ≤ 149 °C; Square-ware pulse	20	А
I _{FSM}	non-repetitive peak	SIN; t_p = 10 ms; $T_{j(init)}$ = 25 °C; per diode; Fig. 4	125	А
	forward current	SIN; t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; per diode	137	А
I _{RRM}	repetitive peak reverse current	δ = 0.001; t_p = 2 µs; per diode	0.2	А
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs; per diode	0.2	А
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C
Electrostat	tic discharge			
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ; all pins	8	kV

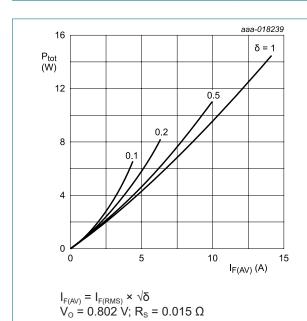
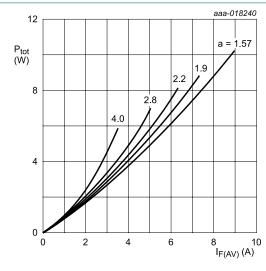


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_{O} = 0.802 V; R_{S} = 0.015 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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Dual ultrafast power diode

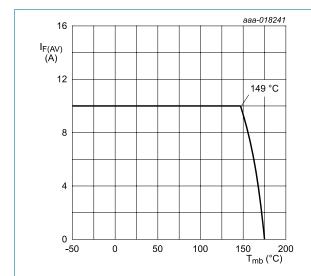


Fig. 3. Forward current as a function of mounting base temperature; maximum values

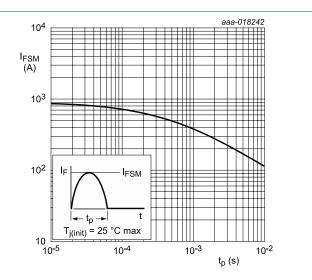


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to	with heatsink compound; both diodes conducting	-	-	1.4	K/W
	mounting base	with heatsink compound; per diode; <u>Fig. 5</u>	-	-	2.4	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

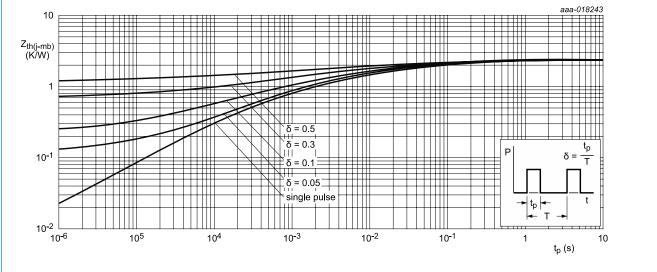
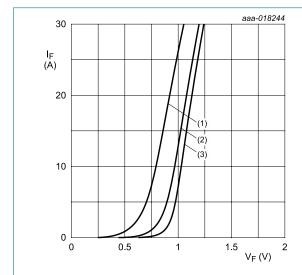


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					•
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>	-	0.76	0.85	V
		I _F = 20 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.06	1.15	V
		I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	0.95	-	V
I_R	reverse current	V _R = 200 V; T _j = 25 °C	-	0.3	5	μA
		V _R = 200 V; T _j = 150 °C	-	70	250	μΑ
Dynamic	characteristics					
Q _r	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	13.5	-	nC
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	-	14.5	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	-	18	25	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s}; $ $T_j = 25 ^{\circ}\text{C}$	-	1.7	-	А



 V_{O} = 0.802 V; R_{S} = 0.015 Ω (1) T_{j} = 150 °C; typical values (2) T_{j} = 150 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 6. Forward current as a function of forward voltage

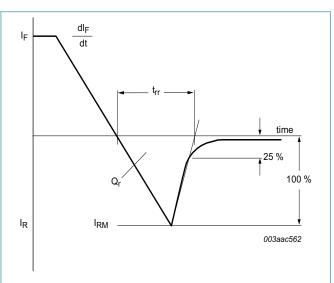
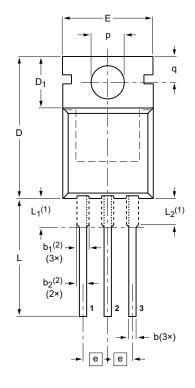


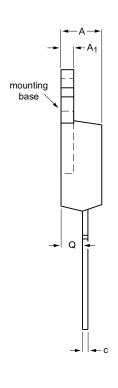
Fig. 7. Reverse recovery definitions; ramp recovery

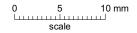
11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78







DIMENSIONS (mm are the original dimensions)

UNIT	А	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13	

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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